

Dual N-Channel Enhancement Mode MOSFET

Features

- Channel 1
30V/7A,
 $R_{DS(ON)} = 22m\Omega$ (typ.) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 26m\Omega$ (typ.) @ $V_{GS} = 4.5V$
- Channel 2
30V/10A,
 $R_{DS(ON)} = 12m\Omega$ (typ.) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 16m\Omega$ (typ.) @ $V_{GS} = 4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

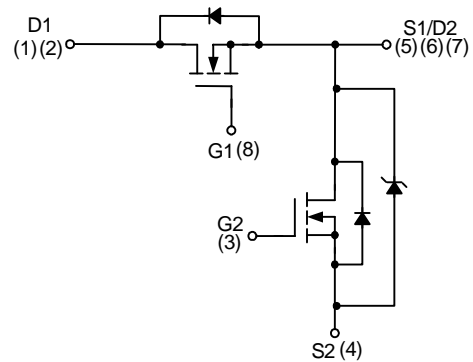
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

Pin Description



Top View of SOP – 8



N-Channel MOSFET

Ordering and Marking Information

<p>APM4910 □□-□□□</p> <div style="margin-left: 20px;"> <p>└─ Lead Free Code</p> <p>└─ Handling Code</p> <p>└─ Temp. Range</p> <p>└─ Package Code</p> </div>	<p>Package Code K : SOP-8</p> <p>Operating Junction Temp. Range C : -55 to 150°C</p> <p>Handling Code TU : Tube TR : Tape & Reel</p> <p>Lead Free Code L : Lead Free Device</p>
<p>APM4910 K : APM4910 XXXXX</p>	<p>XXXXX - Date Code</p>

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Channel 1	Channel 2	Unit
V_{DSS}	Drain-Source Voltage	30	30	V
V_{GSS}	Gate-Source Voltage	± 16	± 20	
I_D^*	Continuous Drain Current	7	10	A
I_{DM}^*	Pulsed Drain Current	25	35	
I_S^*	Diode Continuous Forward Current	2.5	3	A
T_J	Maximum Junction Temperature	150		$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150		
P_D^*	Power Dissipation	$T_A=25^\circ\text{C}$	2	W
		$T_A=100^\circ\text{C}$	0.8	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	62.5		$^\circ\text{C}/\text{W}$

Note:

*Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Channel 1

Symbol	Parameter	Test Condition	Channel 1			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =85°C			1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.5	2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =7A V _{GS} =4.5V, I _{DS} =5A		22 26	28 34	mΩ
V _{SD} ^a	Diode Forward Voltage	I _{SD} =2.5A, V _{GS} =0V		0.8	1.1	V
Gate Charge Characteristics^b						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =7A		10	14	nC
Q _{gs}	Gate-Source Charge			1.5		
Q _{gd}	Gate-Drain Charge			5		
Dynamic Characteristics^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1.5		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		880		pF
C _{oss}	Output Capacitance			125		
C _{rss}	Reverse Transfer Capacitance			90		
t _{d(ON)}	Turn-on Delay Time		V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω		6	12
t _r	Turn-on Rise Time			11	21	
t _{d(OFF)}	Turn-off Delay Time			27	50	
t _f	Turn-off Fall Time			5	10	

Notes:

- a : Pulse test ; pulse width≤300μs, duty cycle≤2%.
- b : Guaranteed by design, not subject to production testing.

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Channel 2

Symbol	Parameter	Test Condition	Channel 2			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$			50	μA
		$T_J=85^\circ\text{C}$			5	mA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1.3	1.8	2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^a$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=10A$		12	15	m Ω
		$V_{GS}=4.5V, I_{DS}=7A$		16	21	
V_{SD}^a	Diode Forward Voltage	$I_{SD}=1A, V_{GS}=0V$			0.52	V
Gate Charge Characteristics^b						
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=4.5V, I_{DS}=10A$		16	22	nC
Q_{gs}	Gate-Source Charge			3.7		
Q_{gd}	Gate-Drain Charge			8.5		
Dynamic Characteristics^b						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.7		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=15V, \text{Frequency}=1.0\text{MHz}$		1610		pF
C_{oss}	Output Capacitance			255		
C_{rss}	Reverse Transfer Capacitance			160		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, R_L=15\Omega, I_{DS}=1A, V_{GEN}=10V, R_G=6\Omega$		10	19	ns
t_r	Turn-on Rise Time			11	21	
$t_{d(OFF)}$	Turn-off Delay Time			39	71	
t_f	Turn-off Fall Time			12	23	

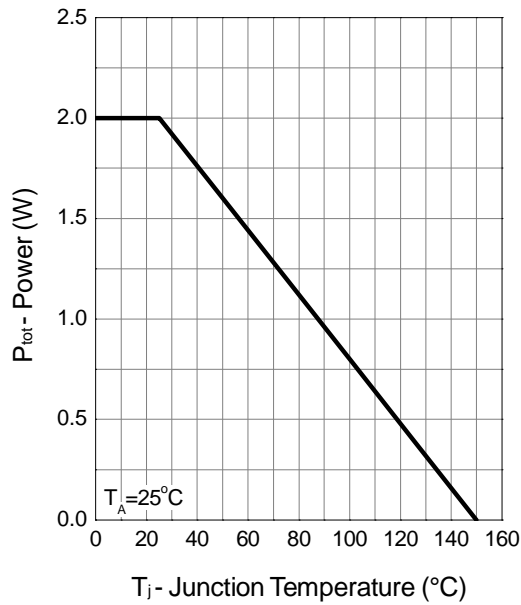
Notes:

- a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- b : Guaranteed by design, not subject to production testing.

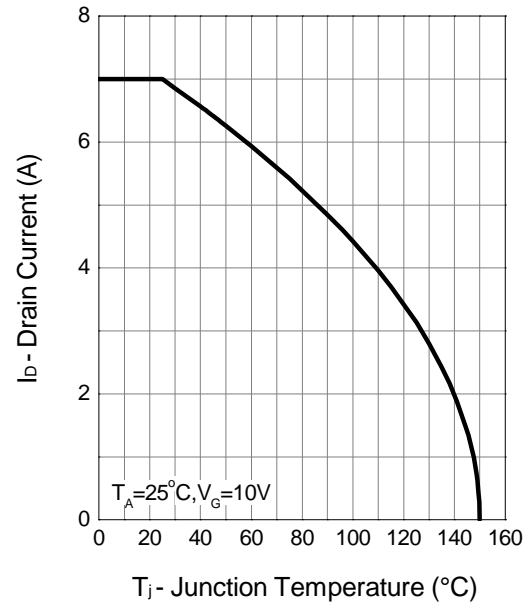
Typical Characteristics

Channel 1

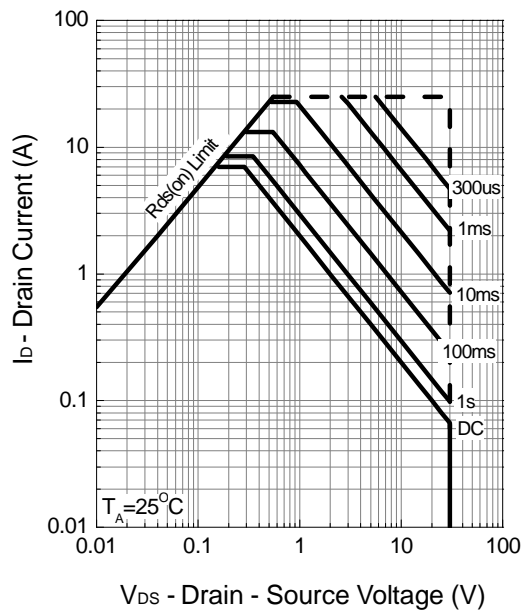
Power Dissipation



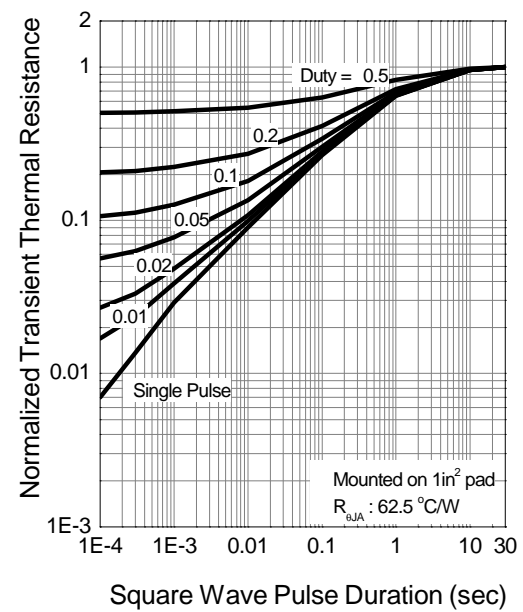
Drain Current



Safe Operation Area



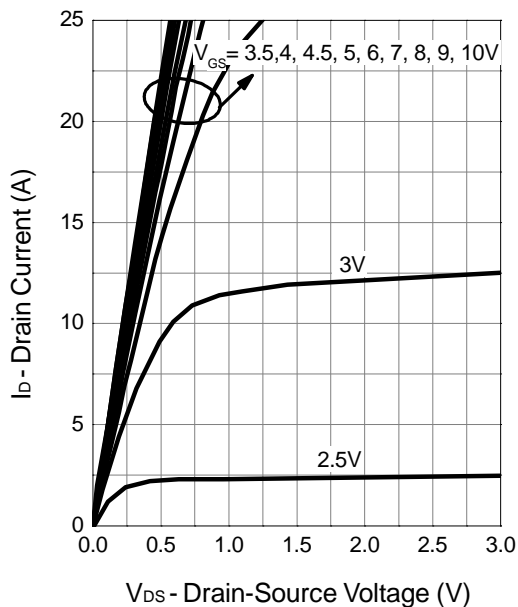
Thermal Transient Impedance



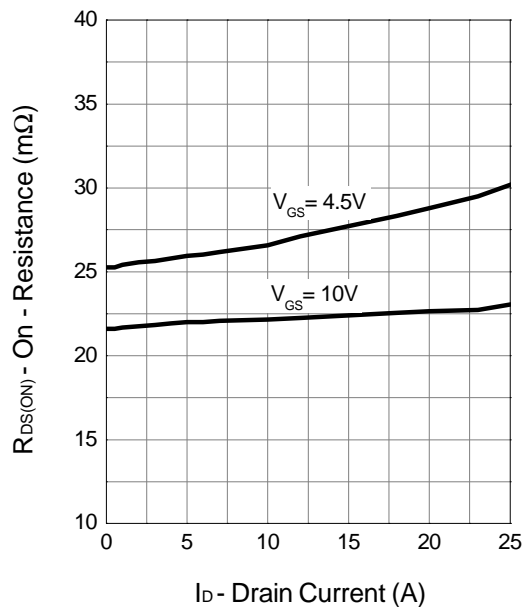
Typical Characteristics (Cont.)

Channel 1

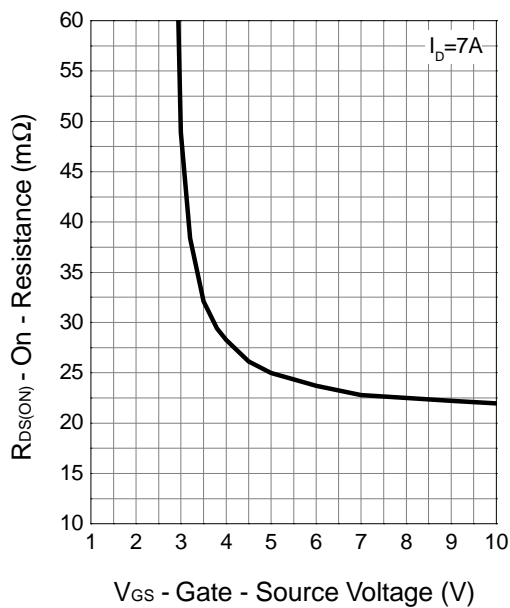
Output Characteristics



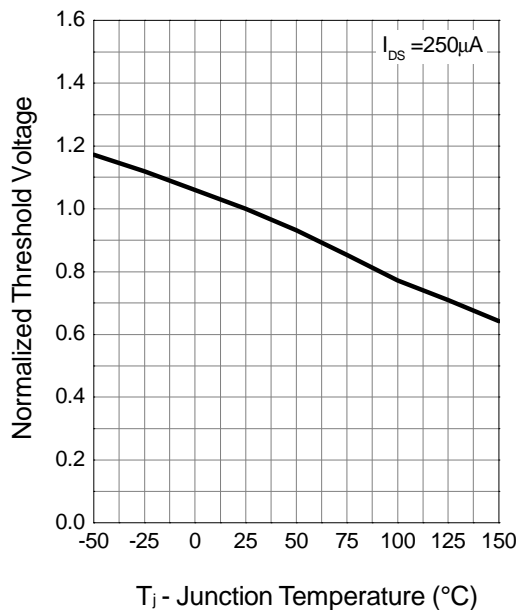
Drain-Source On Resistance



Drain-Source On Resistance



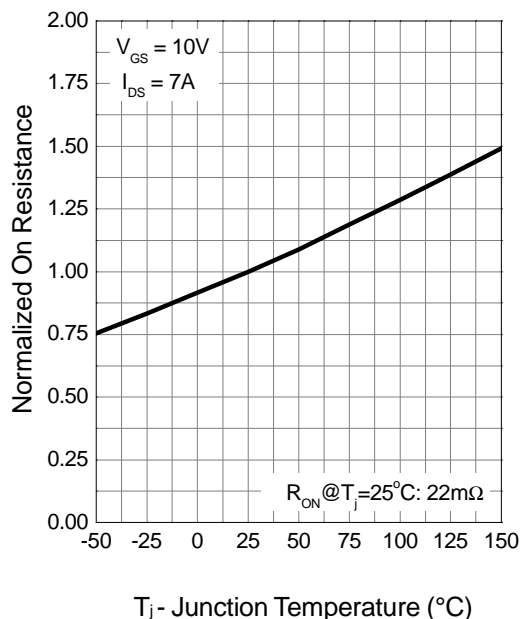
Gate Threshold Voltage



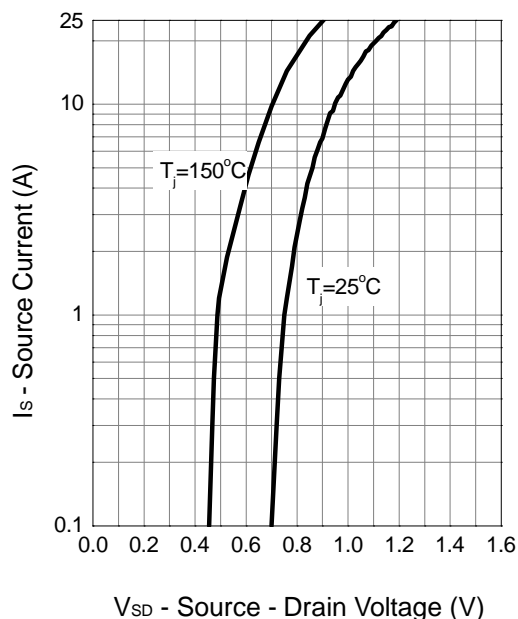
Typical Characteristics (Cont.)

Channel 1

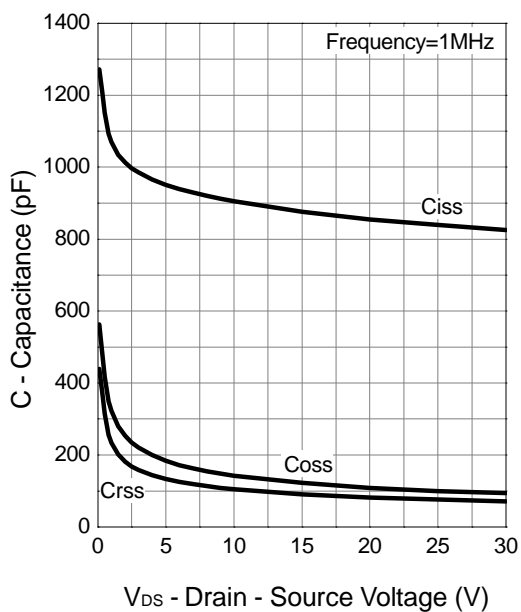
Drain-Source On Resistance



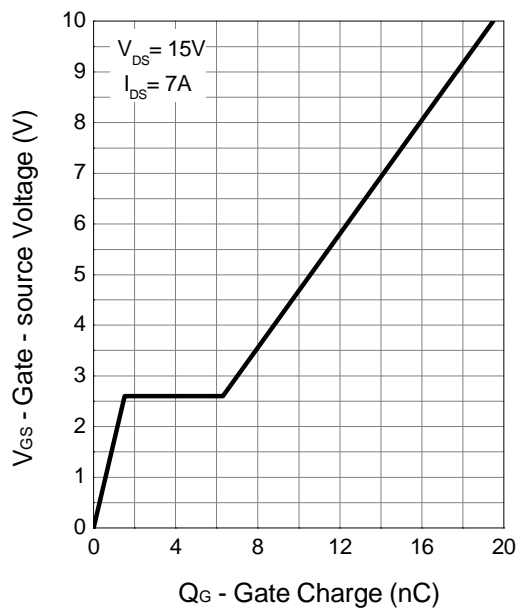
Source-Drain Diode Forward



Capacitance



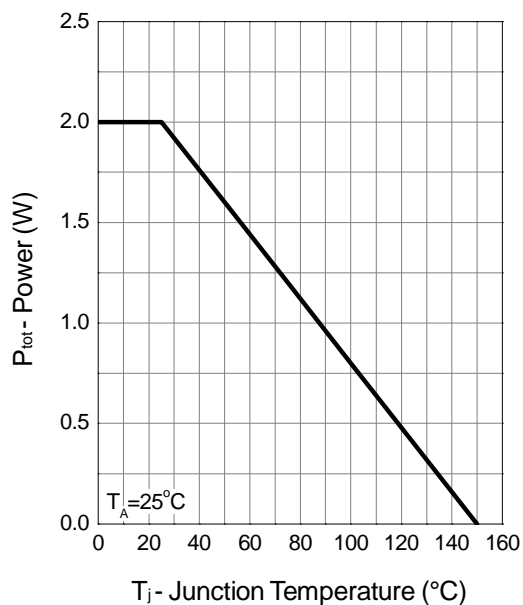
Gate Charge



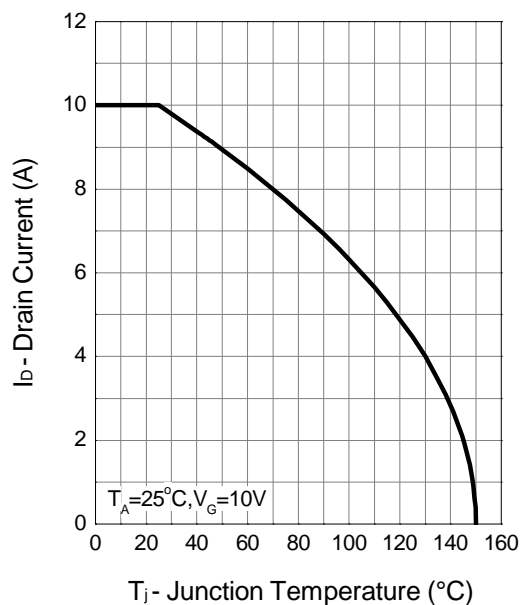
Typical Characteristics (Cont.)

Channel 2

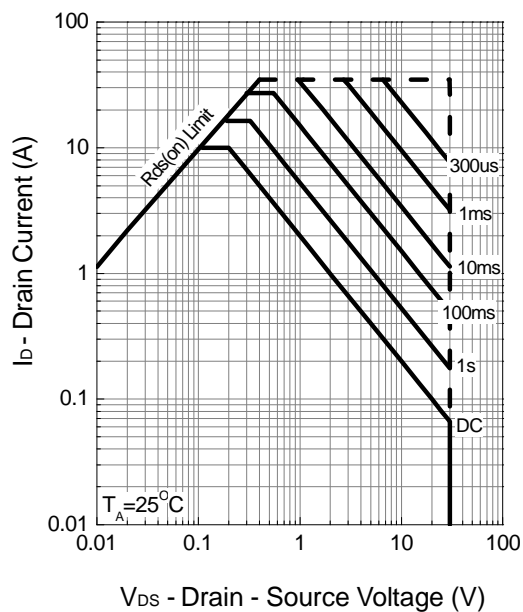
Power Dissipation



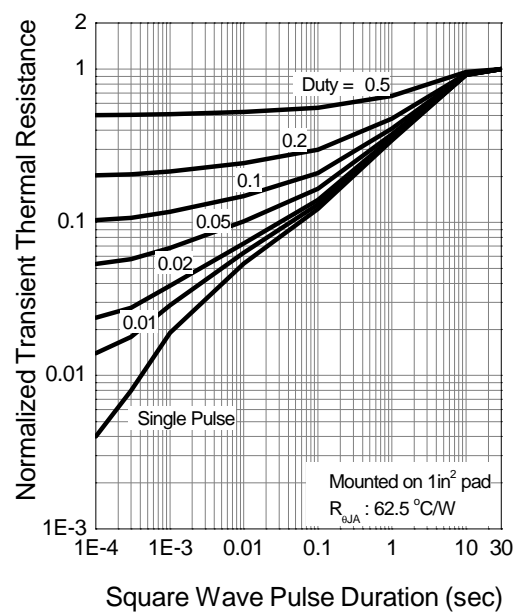
Drain Current



Safe Operation Area



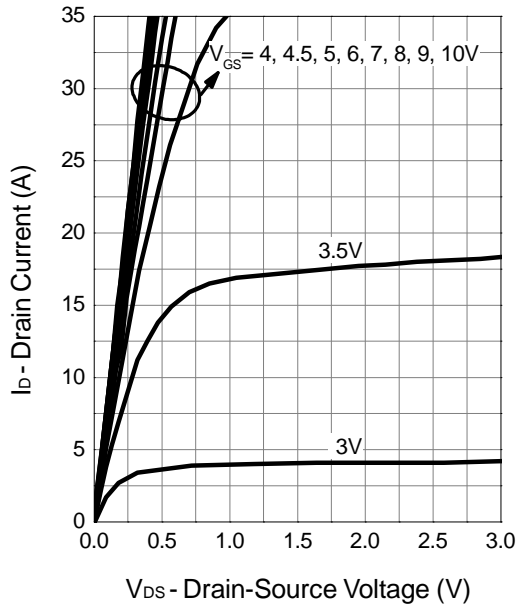
Thermal Transient Impedance



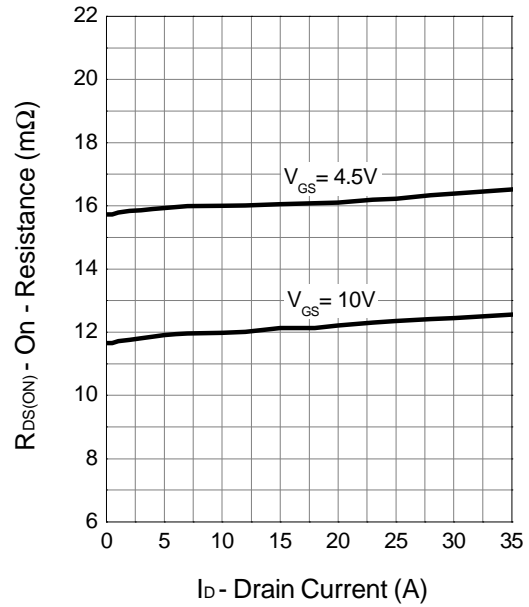
Typical Characteristics (Cont.)

Channel 2

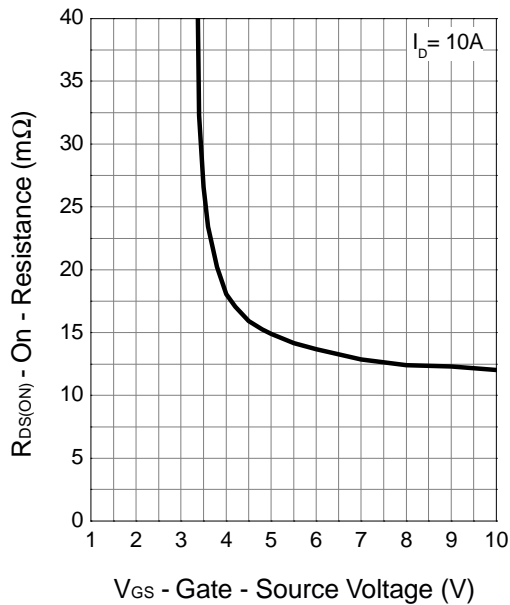
Output Characteristics



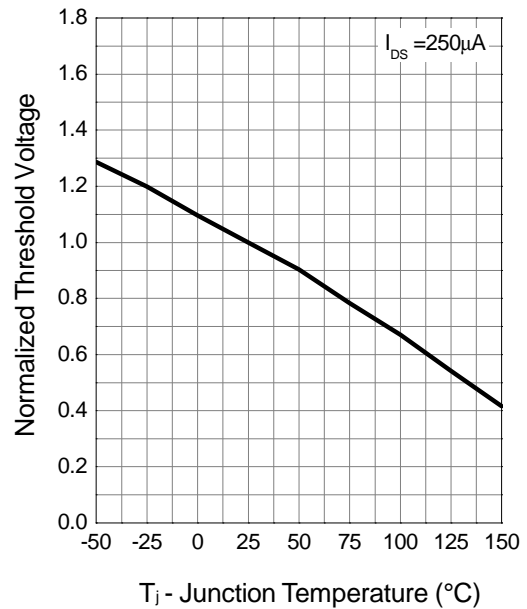
Drain-Source On Resistance



Drain-Source On Resistance



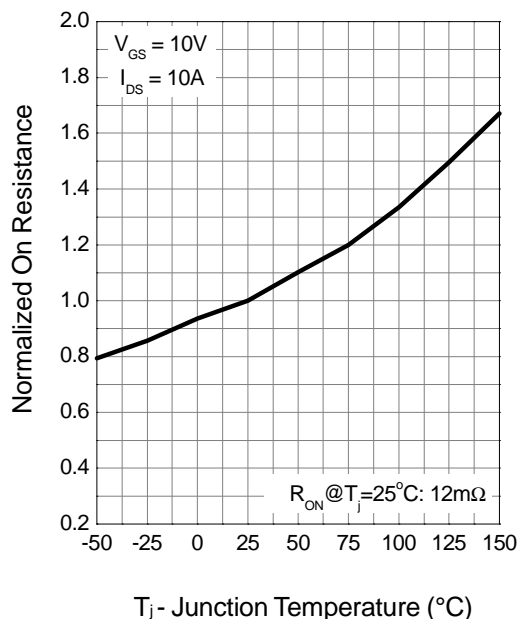
Gate Threshold Voltage



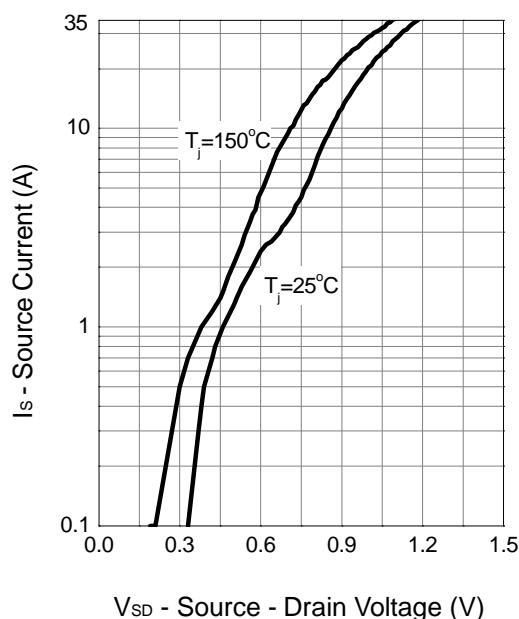
Typical Characteristics (Cont.)

Channel 2

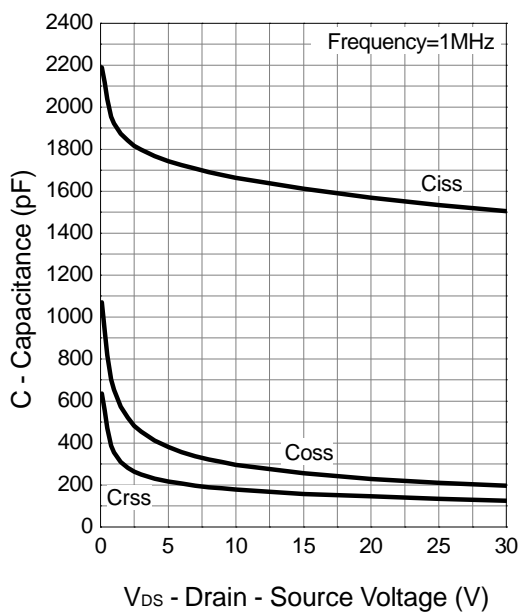
Drain-Source On Resistance



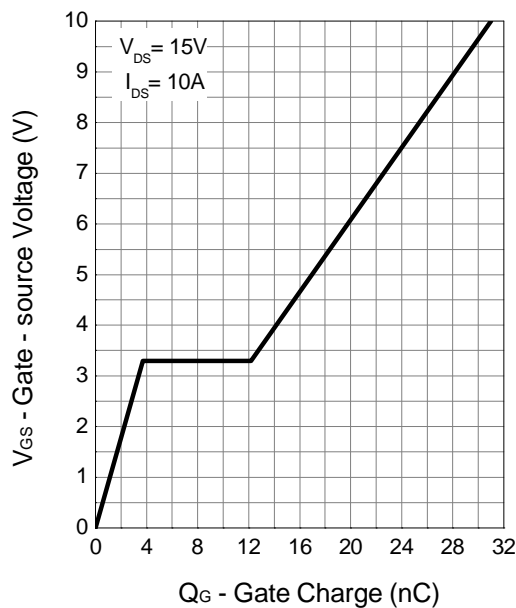
Source-Drain Diode Forward



Capacitance

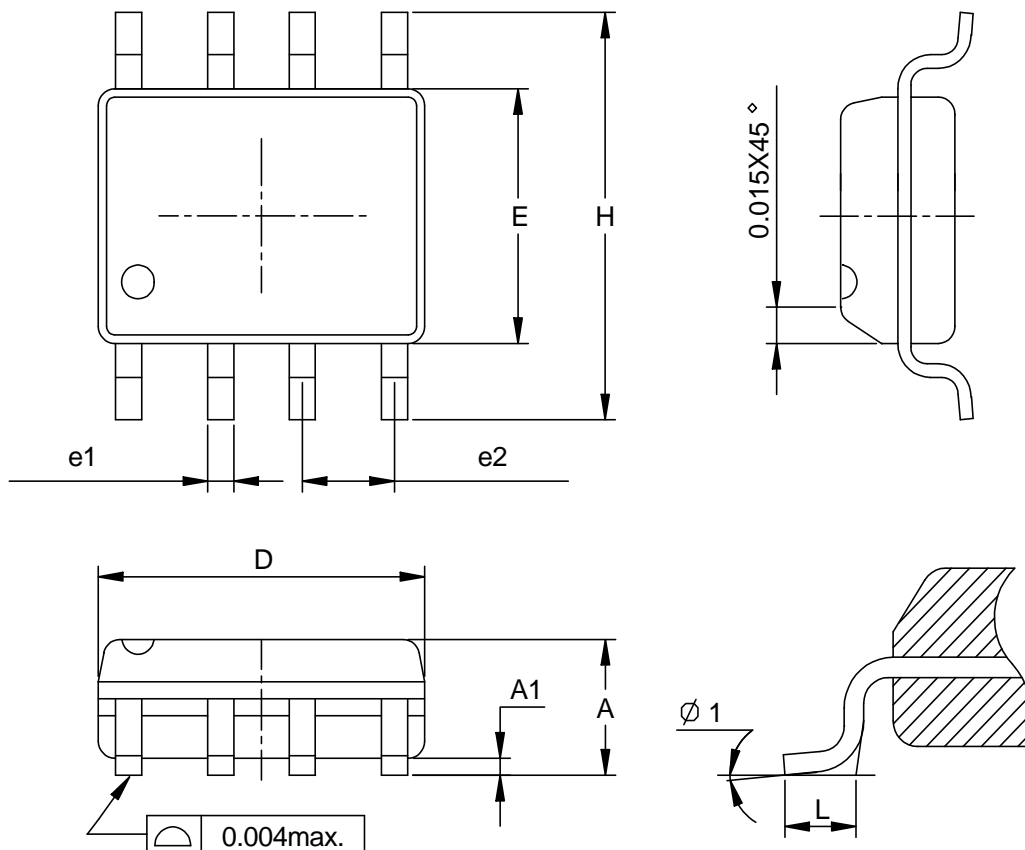


Gate Charge



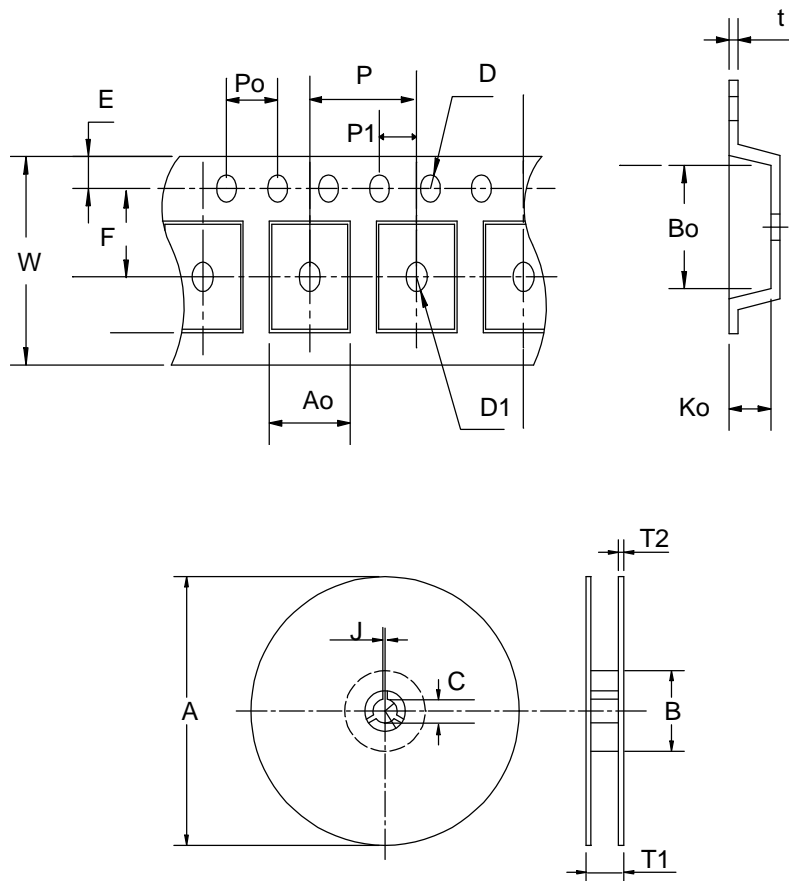
Packaging Information

SOP-8 pin (Reference JEDEC Registration MS-012)



Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	5.00	0.189	0.197
E	3.80	4.00	0.150	0.157
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
e1	0.33	0.51	0.013	0.020
e2	1.27BSC		0.50BSC	
φ 1	0°	8°	0°	8°

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
SOP-8	330±1	62 ± 1.5	12.75 + 0.15	2 + 0.5	12.4 +0.2	2± 0.2	12 + 0.3 - 0.1	8± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5 ± 0.1	1.55±0.1	1.55+ 0.25	4.0 ± 0.1	2.0 ± 0.1	6.4 ± 0.1	5.2± 0.1	2.1± 0.1	0.3±0.013

(mm)

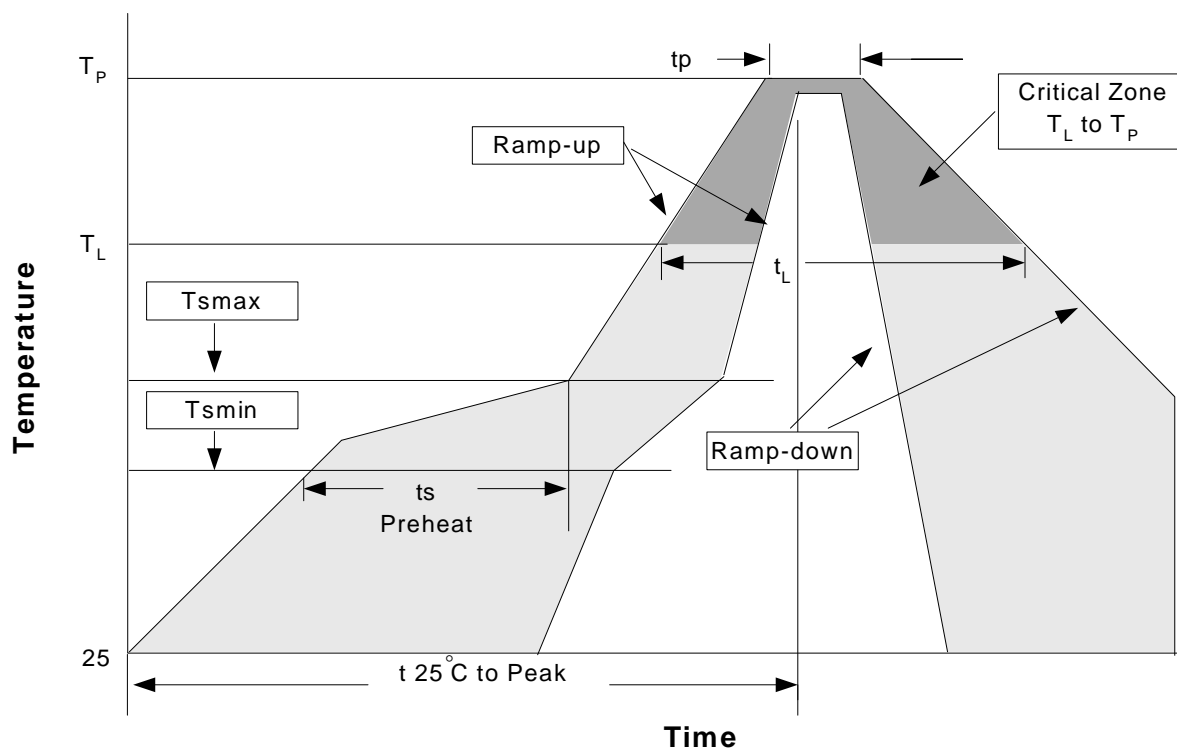
Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOP- 8	12	9.3	2500

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60-120 seconds	60-180 seconds
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60-150 seconds	60-150 seconds
Peak/Classification Temperature (T_p)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t_p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Entectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

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